

Full Bridge PWM Control DC Motor Driver ICs SI-5300

Features

- P-ch MOS for high side and N-ch MOS for low side in one package
- Enable to drive DC±5V
- Possible to drive a motor at the LS-TTL, C-MOS Logic level
- Guarantee $T_j=T_{ch}=150^{\circ}\text{C}$
- Built-in over current protection and thermal shut down circuits
- Built-in diagnosis function to monitor and signal the state of each protection circuits
- Built-in vertical current prevention circuits (Dead time is defined internally.)
- No insulator required for Sanken's original package (SPM package)

Absolute Maximum Ratings

($T_a=25^{\circ}\text{C}$)

Parameter	Symbol	Ratings	Unit	Conditions
Motor supply voltage	V_M	40	V	
Input terminal voltage	IN1	-0.3 to 7	V	
	IN2	-0.3 to 7	V	
	PWM	-0.3 to 7	V	
Output current	I_O	±5	A	
	$I_{O(p-p)}$	±17	A	$P_W \leq 1\text{ms}$, Duty $\leq 50\%$
PWM control frequency	f_{PWM}	20	kHz	Duty=20% to 80%
Forward • reverse rotation switch frequency*	f_{CW}	500	Hz	
Operating temperature	T_{OP}	-40 to +85	$^{\circ}\text{C}$	
Junction and channel temperature	T_j, T_{ch}	-40 to +150	$^{\circ}\text{C}$	
Storage temperature	T_{stg}	-40 to +150	$^{\circ}\text{C}$	
Thermal resistance	θ_{j-c}	3.7	$^{\circ}\text{C/W}$	
	θ_{j-a}	35	$^{\circ}\text{C/W}$	
Power dissipation	P_{D1}	3.6	W	Without heatsink
	P_{D2}	33.7	W	With infinite heatsink

Note: * The dead time for the length current prevention in positive and the reversing switch is set by internal control IC. The set point in internal IC at the dead time is 20μs (typical). Please take into account the dead time and consider the load conditions when you use the IC.

Electrical Characteristics

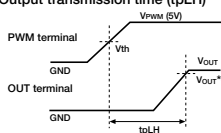
(Unless, otherwise specified, $T_j=T_{ch}=25^{\circ}\text{C}$, $V_M=14\text{V}$, $I_O=3\text{A}$)

Parameter	Symbol	Ratings			Unit	Conditions
		min	typ	max		
Motor supply voltage	V_{IN}	6		18	V	$V_M=24\text{V}$ (2 min.)
Output saturation voltage	V_i, V_M-V_O			0.8	V	$I_O=3\text{A}$
	V_i, V_O-PG			0.3	V	$I_O=3\text{A}$
Output leakage current	$I_{L, L}$		100		μA	$V_M=40\text{V}$
	$I_{L, H}$		100		μA	$V_M=40\text{V}$
Output transmission time	tpLH			10 *2	μs	$V_{PWM}: L \rightarrow H$ ($V_{th}=2.5\text{V}$ typ)
	tpHL			15 *3	μs	$V_{PWM}: H \rightarrow L$ ($V_{th}=2.5\text{V}$ typ)
	tpHL-tpLH			10	μs	
Forward voltage characteristic of diode between drain and source	$V_F \cdot L$		0.8		V	$I_O=3\text{A}$
	$V_F \cdot H$		1.0		V	$I_O=10\text{A}$
			0.8		V	$I_O=3\text{A}$
Static circuit current	IM1		22		mA	Stop mode
	IM2		22		mA	Forward and reverse mode
	IM3		16		mA	Brake mode
Input terminal voltage	$V_{IN, H}$	3.0			V	$V_{IN1}=V_{IN2}=V_{PWM}$
	$V_{IN, L}$			2.0	V	$V_{IN1}=V_{IN2}=V_{PWM}$
Input terminal current	$I_{IN, L}$	-100			μA	$V_{IN1}=V_{IN2}=V_{PWM}=0\text{V}$
	$I_{IN, H}$			200	μA	$V_{IN1}=V_{IN2}=V_{PWM}=5\text{V}$
OPC start current	I_{OCP}	16			A	*1
DIAG output pulse width	t_{DIAG}	20			ms	$C=1\mu\text{F}$ (typ)
DIAG terminal voltage	$V_D \cdot L$			0.3	V	$I_D = \text{SINK} = 1\text{mA}$ *4

Note:

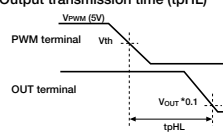
*1: The standard value of I_{OCP} is assumed to be a value by which the output of each Power MOS FET cuts off. When the protection circuit of OCP and TSD operates, Power MOS FETs keeps cutoff. When a signal (5V: H → 0V: L) is input to the terminal PWM, the cutoff operation will be released. Moreover, three minutes ($T_a=25^{\circ}\text{C}$, $f_{PWM}=10\text{kHz}$, $V_M=14\text{V}$) are assumed to be max at the overcurrent state continuance time in the V_M operation and the ground of output terminal (OUT1, OUT2). It is not the one to assure the operation including reliability in the state that the short-circuit continues for a long time.

*2: Output transmission time (tpLH)



Output transmission time tpLH is time from V_{th} (2.5V typ) of the terminal of PWM to output ($V_{OUT} * 0.9$) of the output terminal.

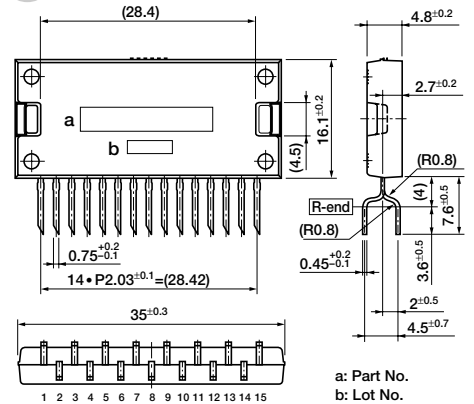
*3: Output transmission time (tpHL)



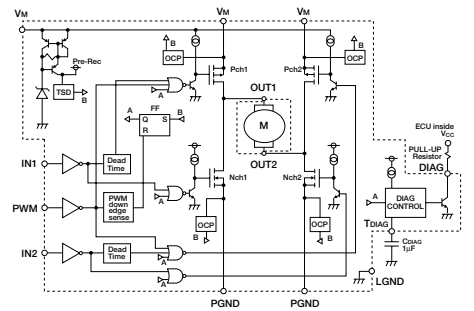
Output transmission time tpHL is time from V_{th} (2.5V typ) of the terminal of PWM to output ($V_{OUT} * 0.1$) of the output terminal.

*4: DIAG signal output terminal is an open collector output. Use a pull-up resistor when connecting it to a logic circuit.

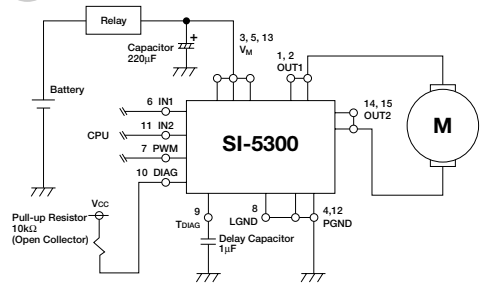
External Dimensions (unit: mm)



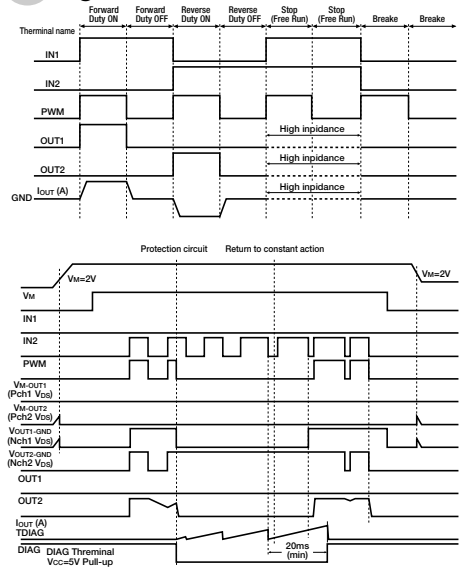
Equivalent Circuit



Standard Connection Diagram

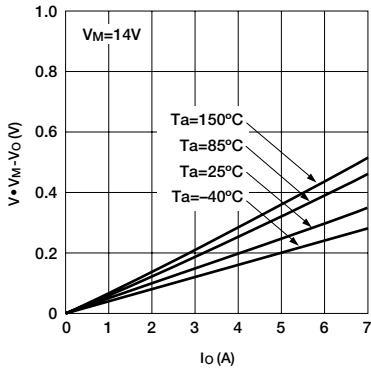


Timing Chart

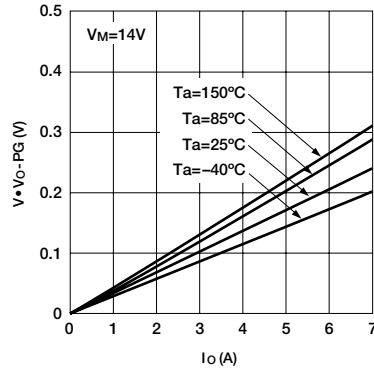


Electrical Characteristics

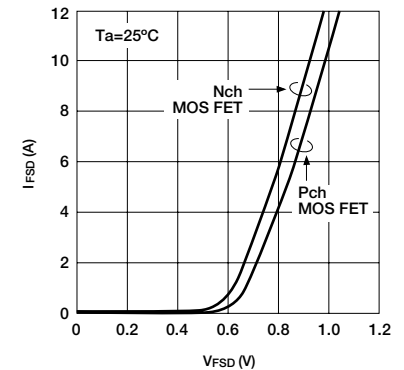
Output saturation voltage (Pch)



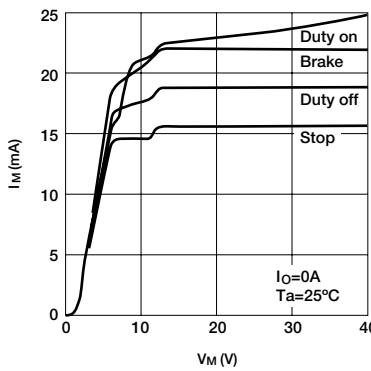
Output saturation voltage (Nch)



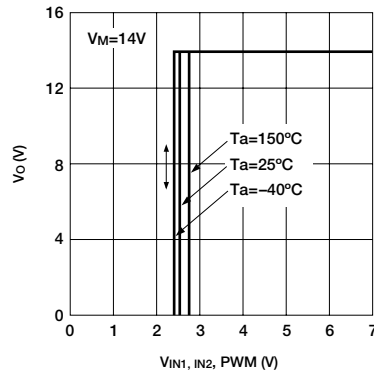
Forward voltage of Diode between drain and source



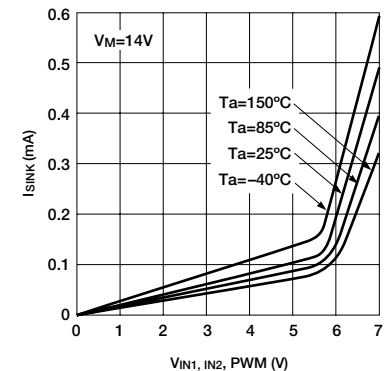
Quiescent circuit current



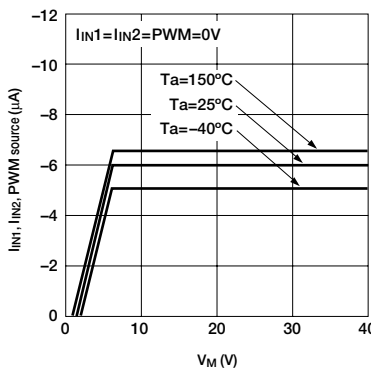
Voltage of input terminal (Threshold voltage)



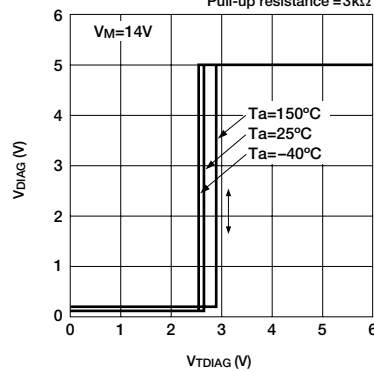
Current of input terminal (SINK current)



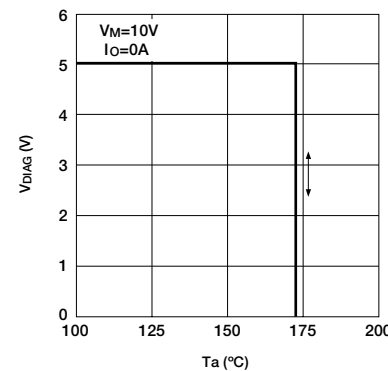
Current of input terminal (Source current)



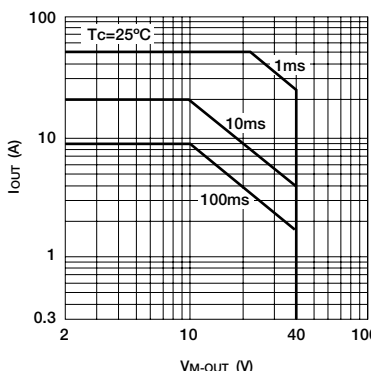
VTDIAG - VDIAG Characteristics



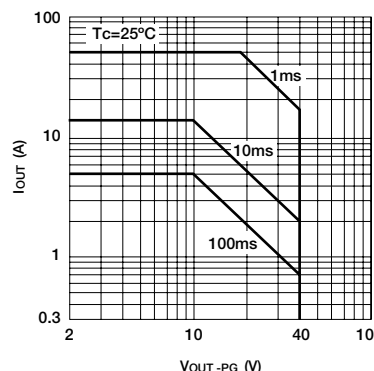
Thermal shut down protection



Pch MOS FET Safe Operating Area (SOA)



Nch MOS FET Safe Operating Area (SOA)



Pd-Ta Characteristics

